



Dr. Kwangmin Park

Advanced Process Development Team,
Semiconductor R&D Center, Samsung, Korea



Kwangmin Park received the B.S. and Ph.D. degrees in Materials Science and Engineering from Seoul National University, Korea, in 2000 and 2005, respectively.

In 2005, he joined Samsung electronics in Korea. From 2005 to 2014, he was involved in research on NAND process technologies such as Charge Trap Flash and dielectric reliability at the Semiconductor Research and Development Center.

From 2015 to 2018, he participated in the development of a new memory for Storage Class Memory. From 2018 to 2022, he developed the NAND device process related to memory cell performance, reliability and quality as a project leader in Process Development Team.

Since 2023, he has led the development of the future materials and processes for next generation of memory and logic transistors as a Master (VP of Technology).